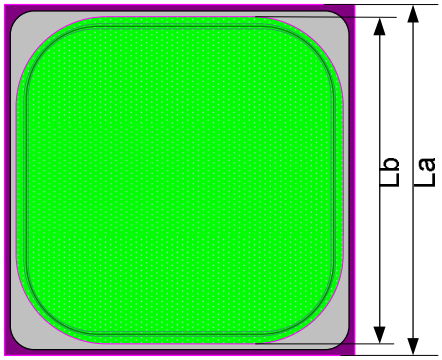
2SF292200CYY ULTRAFAST RECOVERY DIODE CHIPS

DESCRIPTION

- Ø 2SF292200CYY is a ultrafast recovery diode chips fabricated in silicon epitaxial planar technology;
- Ø Ultrafast recovery times;
- Ø High current capability;
- Ø High surge current capability;
- Ø Low forward voltage drop;
- Ø Low reverse current leakage;
- Ø Top metal is Ag, Back metal is Ag;
- Ø Chip Size: 2920μm X 2920μm;
- Ø Chip Thickness: 280±20μm;



Chip Topography and Dimensions

La: Chip Size:2920 μm;

Lb: Pad Size: 2840 μm;

ORDERING SPECIFICATIONS

Product Name	Specification
2SF292200CYY	For Au and AlSi wire bonding package

ABSOLUTE MAXIMUM RATINGS

Parameters	Symbol	Ratings	Unit
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	200	V
Average Forward RectifiedCurrent@Tc=150°C	I_{FAV}	15	A
Peak Forward Surge Current@8.3ms	I_{FSM}	200	A
Maximum Operation Junction Temperature	T_J	175	°C
Storage Temperature Range	T_{STG}	-55~175	°C

ELECTRICAL CHARACTERISTICS (T_{amb}=25℃)

Parameters	Symbol	Test Conditions	Min.	Max.	Unit
Reverse Voltage	V_{BR}	I_R=50μA	200	--	V
Forward Voltage	V_F	I_F=15A	--	1.05	V
Reverse Current	I_R	V_R=200V	--	10	μA
Reverse recovery time	Trr	I_F=1A,di/dt=50A/μs	--	35	ns